

IN THE SPECIFICATION:

On Page 1, below the title, insert the following:

--RELATED APPLICATION

This application is a divisional application of U.S. Patent Application Serial No. 10/061,365, filed February 4, 2002. --

On Page 6 of the specification, change the paragraph starting at line 20 as follows:

--Preferably, the first semiconductor layer is a Si layer, and the second semiconductor layer is a $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ layer ($0 < x < 1$, $0 < y < 1$, $0 < x + y < 1$). As a result, excellent characteristics can be obtained using a hetero junction.--

On Page 7 of the specification, change the paragraph starting at line 18 as follows:

--Preferably, the third and fourth semiconductor layers each including a $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$ layer ($0 < x < 1$, $0 < y < 1$, $0 < x + y < 1$) are formed in the step (b). This enables formation of a semiconductor device including a bipolar transistor having excellent frequency characteristics and a variable capacitor having a large variation range of capacitance.--